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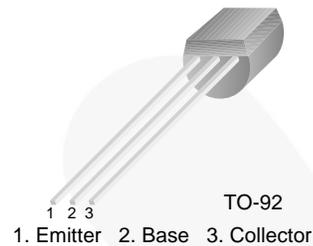
November 2014

KSP2222A

NPN General-Purpose Amplifier

Features

- Collector-Emitter Voltage: $V_{CEO} = 40\text{ V}$
- Available as PN2222A



Ordering Information

Part Number	Marking	Package	Packing Method
KSP2222ABU	KSP2222	TO-92 3L	Bulk
KSP2222ATA	KSP2222	TO-92 3L	Ammo
KSP2222ATF	KSP2222	TO-92 3L	Tape and Reel

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current	600	mA
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 to +150	$^\circ\text{C}$

Thermal Characteristics⁽¹⁾Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation by $R_{\theta JA}$	625	mW
	Derate Above 25°C	5	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	83.3	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	$^\circ\text{C}/\text{W}$

Note:

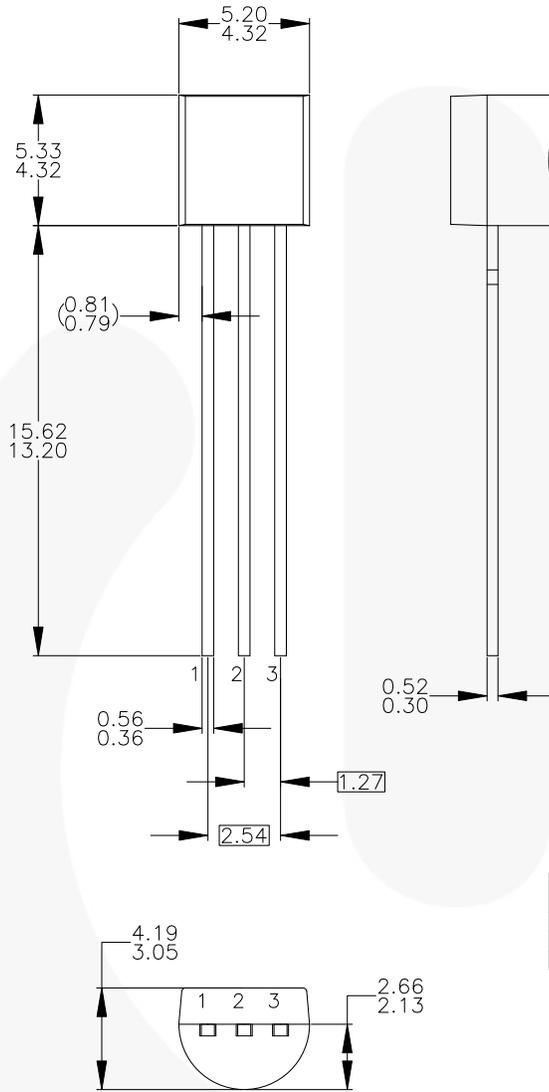
1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical CharacteristicsValues are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	75		V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	40		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 60 \text{ V}, I_E = 0$		0.01	μA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 3.0 \text{ V}, I_C = 0$		10	nA
h_{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ mA}$	35		
		$V_{CE} = 10 \text{ V}, I_C = 1 \text{ mA}$	50		
		$V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$	75		
		$V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}^{(2)}$	100	300	
		$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}^{(2)}$	40		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ⁽²⁾	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$		0.3	V
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.0	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ⁽²⁾	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	0.6	1.2	V
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		2.0	
f_T	Current Gain Bandwidth Product	$I_C = 20 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$	300		MHz
C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		8	pF
t_{ON}	Turn-On Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = 15 \text{ mA}, V_{BE(off)} = 0.5 \text{ V}$		35	ns
t_{OFF}	Turn-Off Time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = I_{B2} = 15 \text{ mA}$		285	ns
NF	Noise Figure	$I_C = 100 \mu\text{A}, V_{CE} = 10 \text{ V}, R_S = 1 \text{ k}\Omega, f = 1.0 \text{ kHz}$		4	dB

Note:2. Pulse test: Pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$

Physical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994.
- D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92			94			96			97			98		
	P	F	M	P	F	M	B	F	M	P	F	M	P	F	M
1	E	S	S	E	S	S	B	D	G	C	G	D	C	G	D
2	B	D	G	C	G	D	E	S	S	B	D	G	E	S	S
3	C	G	D	B	D	G	C	G	D	E	S	S	B	D	G

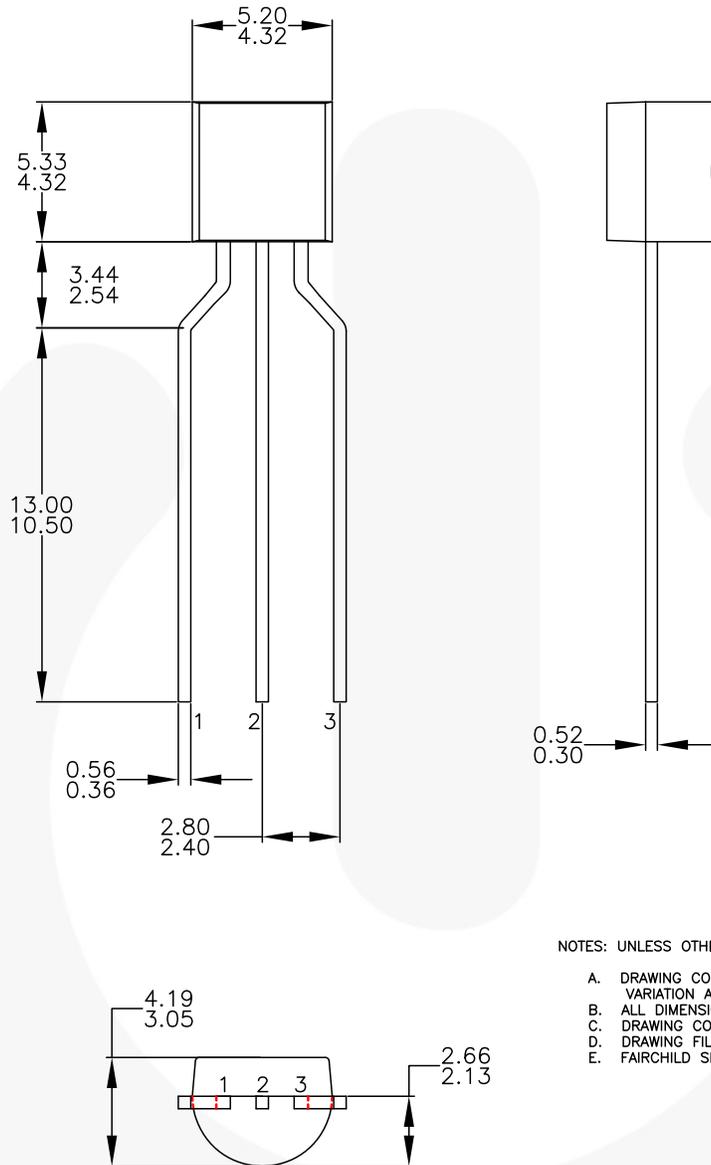
LEGEND:

- P - BIPOLAR
- F - JFET
- M - DMOS
- E - EMITTER
- B - BASE
- C - COLLECTOR
- D - DRAIN
- S - SOURCE
- G - GATE

- E) FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "D" AND SOURCE "S" ARE INTERCHANGEABLE AT JFET "F" OPTION.
- F) DRAWING FILENAME: MKT-ZA03DREV3.

Figure 1. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

Physical Dimensions (Continued)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.

Figure 2. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type